

EM1B ~ EM1C

SILICON RECTIFIER DIODES

PRV : 800 ~ 1000 Volts

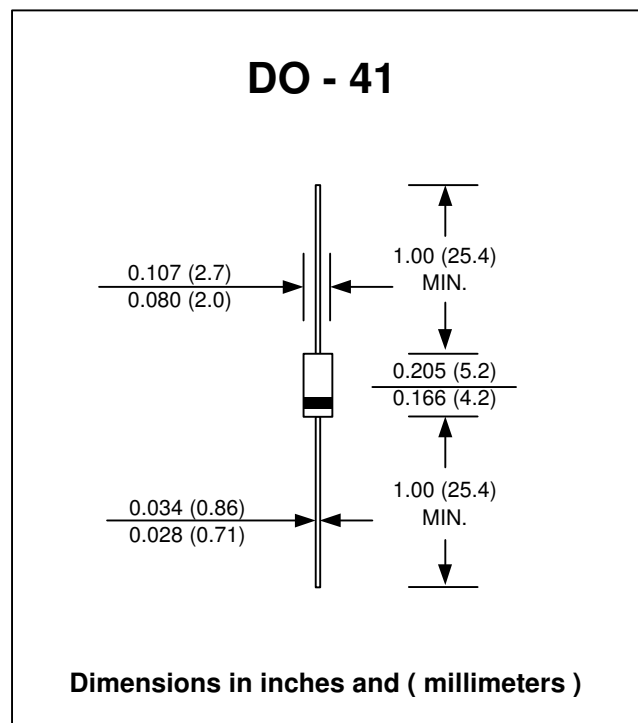
Io : 1.0 Ampere

FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : DO-41 Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.339 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

RATING	SYMBOL	EM1B	EM1C	UNIT
Maximum Peak Reverse Voltage	V_{RM}	800	1000	V
Maximum Peak Reverse Surge Voltage	V_{RSM}	850	1050	V
Maximum Reverse Voltage	V_R	800	1000	V
Maximum Average Forward Current	$I_{F(AV)}$	1.0		A
Maximum Peak Forward Surge Current (50 Hz, Half-cycle, Sine Wave, Single Shot)	I_{FSM}	35		A
Maximum Forward Voltage at $I_F = 1.0$ A	V_F	0.97		V
Maximum Reverse Current at Reverse Voltage $T_a = 25$ °C	I_R	20		μA
Maximum Reverse Current at Reverse Voltage $T_a = 100$ °C	$I_{R(H)}$	100		μA
Junction Temperature Range	T_J	- 40 to + 150		°C
Storage Temperature Range	T_{STG}	- 40 to + 150		°C

RATING AND CHARACTERISTIC CURVES (EM1B ~ EM1C)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

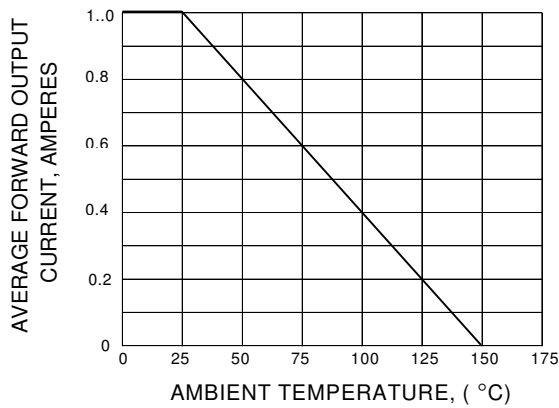


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

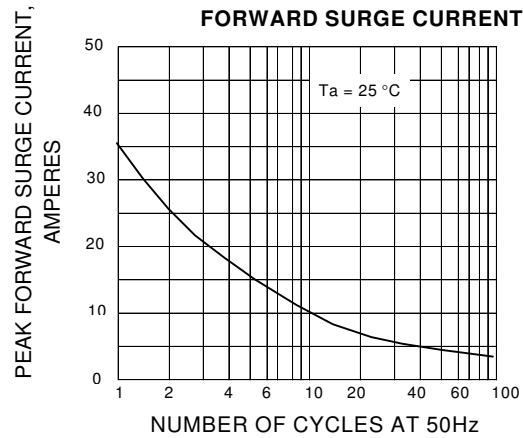


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

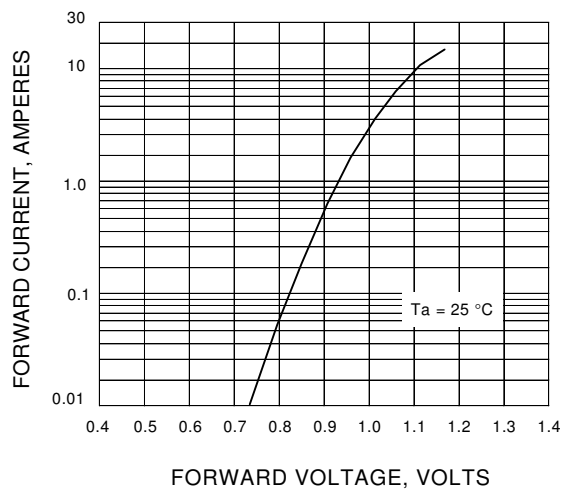


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

